The LMV931 Single and LMV932 Dual are CMOS low-voltage operational amplifiers which can operate on single-sided power supplies (1.8 V to 5.0 V) with rail-to-rail input and output swing. Both devices come in small state-of-the-art packages and require very low quiescent current making them ideal for battery-operated, portable applications such as notebook computers and hand-held instruments. Rail-to-Rail operation provides improved signal-to-noise performance plus the small packages allow for closer placement to signal sources thereby reducing noise pickup.

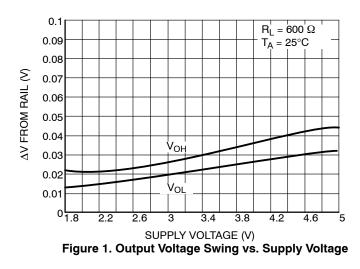
The single LMV931 is offered in space saving SC70-5 package. The dual LMV932 is in either a Micro8 or SOIC package. These small packages are very beneficial for crowded PCB's.

Features

- Performance Specified on Single-Sided Power Supply: 1.8 V, 2.7 V, and 5V
- Small Packages: LMV931 in a SC-70 LMV932 in a Micro8 or SOIC-8
- No Output Crossover Distortion
- Extended Industrial Temperature Range: -40°C to +125°C
- Low Quiescent Current 210 μA, Max Per Channel
- No Output Phase-Reversal from Overdriven Input
- These are Pb-Free Devices

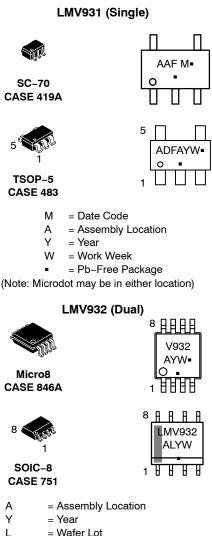
Typical Applications

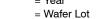
- Notebook Computers, Portable Battery-Operated Instruments, PDA's
- Active Filters, Low-Side Current Monitoring











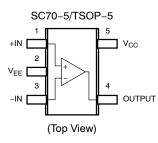
- = Work Week
- W = Pb-Free Package

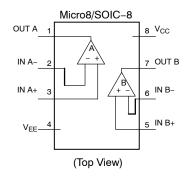
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 14 of this data sheet.

PIN CONNECTIONS





MAXIMUM RATINGS

Symbol	Rating		Value	Unit
Vs	Supply Voltage (Operating Range V_S = 1.8 V to 5.5 V)	5.5	V	
V _{IDR}	Input Differential Voltage	± Supply Voltage	V	
VICR	Input Common Mode Voltage Range	–0.5 to (V _{CC}) + 0.5	V	
	Maximum Input Current	10	mA	
t _{So}	Output Short Circuit (Note 1)		Continuous	
TJ	Maximum Junction Temperature (Operating Range -40°C to 85°C	;)	150	°C
θ_{JA}	Thermal Resistance: S TS N	280 333 238	°C/W	
T _{stg}	Storage Temperature		–65 to 150	°C
	Mounting Temperature (Infrared or Convection \leq 30 sec)		260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ESD data available upon request.

 Continuous short-circuit operation to ground at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C. Output currents in excess of 45 mA over long term may adversely affect reliability. Shorting output to either V_{CC} or V_{EE} will adversely affect reliability.

1.8 V DC ELECTRICAL CHARACTERISTICS (Note 2) Unless otherwise noted, all min/max limits are guaranteed for T _A = 25°C,
V_S = 1.8 V, V_{CM} = $V_S/2$, V_O = $V_S/2$ and R_L > 1 M Ω . Typical specifications represent the most likely parametric norm.

Parameter	Parameter Symbol Condition		Min	Тур	Max	Unit
Input Offset Voltage	V _{IO}	LMV931 (Single) (-40°C to +125°C)		1	6	mV
		LMV932 (Dual) (-40°C to +125°C)		1	7.5	
Input Offset Voltage Average Drift	TCV _{IO}			5.5		μV/°C
Input Bias Current	Ι _Β	-40°C to +125°C		< 1		nA
Input Offset Current	I _{IO}	-40°C to +125°C		< 1		nA
Supply Current	I _{CC}	In Active Mode		75	185	μA
(per Channel)		-40°C to +125°C			205	
Common Mode	CMRR	0 V \leq V_{CM} \leq 0.6 V, 1.4 V \leq V_{CM} \leq 1.8 V	50	70		dB
Rejection Ratio		– 40°C to +125°C	50			-
		$-0.2 \text{ V} \leq \text{V}_{CM} \leq 0 \text{ V}, 1.8 \text{ V} \leq \text{V}_{CM} \leq 2 \text{ V}$	50	70		
Power Supply	PSRR	1.8 V \leq V ⁺ \leq 5 V, V _{CM} = 0.5 V	50	70		dB
Rejection Ratio		-40°C to +125°C	50			
Input Common–Mode Voltage Range	Vсм	For CMRR \geq 50 dB and T _A = 25°C	V _{EE} - 0.2	-0.2 to 2.1	V _{CC} + 0.2	V
		For CMRR \geq 50 dB and T _A = - 40°C to +85°C	V_{EE}		V _{CC}	-
		For CMRR \geq 50 dB and T _A = - 40°C to +125°C	V _{EE} + 0.2		V _{CC} - 0.2	
Large Signal Voltage Gain LMV931 (Single)	A _V	$\rm R_L$ = 600 Ω to 0.9 V, V_O = 0.2 V to 1.6 V, V_{CM} = 0.5 V	77	101		dB
		-40°C to +125°C	73			-
		R_L = 2 k Ω to 0.9V, V_O = 0.2 V to 1.6 V, V_{CM} = 0.5 V	80	105		
		-40°C to +125°C	75			
Large Signal Voltage		${\sf R}_L$ = 600 Ω to 0.9 V, ${\sf V}_O$ = 0.2 V to 1.6 V, ${\sf V}_{CM}$ = 0.5 V	75	90		
Gain LMV932 (Dual)		-40°C to +125°C	72			
		R_L = 2 k Ω to 0.9 V, V_O = 0.2 V to 1.6 V,V_{CM} = 0.5 V	78	100		
		-40°C to +125°C	75			
Output Swing	V _{OH}	R_L = 600 Ω to 0.9V, V_{IN} = $\pm100~mV$	1.65	1.72		V
		-40°C to +125°C	1.63			
	V _{OL}	$\rm R_L$ = 600 Ω to 0.9V, $\rm V_{\rm IN}$ = $\pm100~mV$		0.077	0.105	
		-40°C to +125°C			0.12	
	V _{OH}	R_L = 2 k Ω to 0.9V, V_{IN} = ±100 mV	1.75	1.77		
		-40°C to +125°C	1.74			
	V _{OL}	$\rm R_L$ = 2 k\Omega to 0.9 V, V_{IN} = $\pm100~mV$		0.24	0.035	
		−40°C to +125°C	1		0.04	
Output Short Circuit	Ι _Ο	Sourcing, Vo = 0 V, V _{IN} = +100 mV	4.0	30		mA
Current		-40°C to +125°C	3.3			
		Sinking, Vo = 1.8V, V _{IN} = -100 mV	7.0	60		
		-40°C to +125°C	5.0	1		1

2. Guaranteed by design and/or characterization.

1.8 V AC ELECTRICAL CHARACTERISTICS Unless otherwise specified, all limits are guaranteed for T_A = 25°C, V_S = 1.8 V, $V_{CM} = V_S/2$, $V_0 = V_S/2$ and $R_L > 1 M\Omega$. Typical specifications represent the most likely parametric norm. Min/Max specifications are guaranteed by testing, characterization, or statistical analysis.

Parameter	Symbol	Condition		Тур	Max	Unit
Slew Rate	SR	(Note 3)		0.35		V/µS
Gain Bandwidth Product	GBWP			1.4		MHz
Phase Margin	Θm			67		0
Gain Margin	Gm			7		dB
Input-Referred Voltage Noise	e _n	f = 50 kHz, V _{CM} = 0.5 V		60		nV/√Hz
Total Harmonic Distortion	THD	f = 1 kHz, A_V = +1, R_L = 600 Ω , V_O = 1 V_{PP}		0.023		%
Amplifier-to-Amplifier Isolation		(Note 4)		123		dB

3. Connected as voltage follower with input step from V_{EE} to V_{CC}. Number specified is the slower of the positive and negative slew rates. 4. Input referred, R_L = 100 k Ω connected to V_S/2. Each amp excited in turn with 1 kHz to produce V_O = 3 V_{PP}. (For Supply Voltages < 3 V, $V_{O} = V_{CC}$).

2.7 V DC ELECTRICAL CHARACTERISTICS (Note 5) Unless otherwise noted, all min/max limits are guaranteed for T _A = 25°C,
$V_{\rm S}$ = 2.7 V, $V_{\rm CM}$ = $V_{\rm S}/2$, $V_{\rm O}$ = $V_{\rm S}/2$ and $R_{\rm L}$ > 1 M Ω . Typical specifications represent the most likely parametric norm.

Parameter Symbo		Condition	Min	Тур	Max	Unit
Input Offset Voltage	V _{IO}	LMV931 (Single) (-40°C to +125°C)		1	6	mV
	-	LMV932 (Dual) (-40°C to +125°C)		1	7.5	
Input Offset Voltage Average Drift	TCV _{IO}			5.5		μV/°C
Input Bias Current	Ι _Β	-40°C to +125°C		< 1		nA
Input Offset Current	I _{IO}	-40°C to +125°C		< 1		nA
Supply Current (per	I _{CC}	In Active Mode		80	190	μA
Channel)	-	-40°C to +125°C			210	
Common Mode	CMRR	0 V \leq V_{CM} \leq 1.5 V, 2.3 V \leq V_{CM} \leq 2.7 V	50	70		dB
Rejection Ratio		-40°C to +125°C	50			1
		-0.2 V \leq V_{CM} \leq 0 V, 2.7 V \leq V_{CM} \leq 2.9 V	50	70		
Power Supply	PSRR	1.8 V \leq V ⁺ \leq 5 V, V _{CM} = 0.5 V	50	70		dB
Rejection Ratio		-40°C to +125°C	50	1		
Input Common-Mode Voltage Range	Vсм	For CMRR \geq 50 dB and T _A = 25°C	V _{EE} - 0.2	-0.2 to 3.0	V _{CC} + 0.2	V
		For CMRR \geq 50 dB and T _A = -40°C to +85°C	V _{EE}		V _{CC}	-
		For CMRR \geq 50 dB and T _A = -40°C to +125°C	V _{EE} + 0.2		V _{CC} - 0.2	
Large Signal Voltage Gain LMV931 (Single)	A _V	R_L = 600 Ω to 1.35 V, V_O = 0.2 V to 2.5 V	87	104		dB
		−40°C to +125°C	86			
		R_L = 2 k Ω to 1.35 V, V_O = 0.2 V to 2.5 V	92	110		
		−40°C to +125°C	91			
Large Signal Voltage	A _V	R_L = 600 Ω to 1.35 V, V_O = 0.2 V to 2.5 V	78	90		
Gain LMV932 (Dual)		-40°C to +125°C	75			
		$R_L{=}~2~k\Omega$ to 1.35 V, V_O = 0.2 V to 2.5 V	81	100		
	-	-40°C to +125°C	78			
Output Swing	V _{OH}	R_L = 600 Ω to 1.35 V, V_{IN} = $\pm100~mV$	2.55	2.62		V
	-	-40°C to +125°C	2.53			
	V _{OL}	R_{L} = 600 Ω to 1.35 V, V_{IN} = $\pm100~mV$		0.083	0.11	
		-40°C to +125°C			0.13	
	V _{OH}	R_L = 2 k\Omega to 1.35 V, V_{IN} = $\pm100~mV$	2.65	2.675		
		-40°C to +125°C	2.64			
	V _{OL}	R_L = 2 k\Omega to 1.35 V, V_{IN} = ±100 mV		0.025	0.04	
		-40°C to +125°C			0.045	
Output Short Circuit	Ι _Ο	Sourcing, Vo = 0 V, V_{IN} = ±100 mV	20	65		mA
Current		-40°C to +125°C	15	1		
		Sinking, Vo = 0 V, V_{IN} = -100 mV	18	75		
		-40°C to +125°C	12			

5. Guaranteed by design and/or characterization.

2.7 V AC ELECTRICAL CHARACTERISTICS Unless otherwise specified, all limits are guaranteed for T_A = 25°C, V_S = 2.7 V, $V_{CM} = V_S/2$, $V_0 = V_S/2$ and $R_L > 1$ M Ω . Typical specifications represent the most likely parametric norm. Min/Max specifications are guaranteed by testing, characterization, or statistical analysis.

Parameter	Symbol	Condition		Тур	Max	Unit
Slew Rate	SR	(Note 6)		0.4		V/uS
Gain Bandwidth Product	GBWP			1.4		MHz
Phase Margin	Θm			70		0
Gain Margin	Gm			7.5		dB
Input-Referred Voltage Noise	e _n	f = 50 kHz, V _{CM} = 1.0 V		57		nV/√Hz
Total Harmonic Distortion	THD	f = 1 kHz, A_V = +1, R_L = 600 Ω , V_O = 1 V_{PP}		0.022		%
Amplifier-to-Amplifier Isolation		(Note 7)		123		dB

6. Connected as voltage follower with input step from V_{EE} to V_{CC}. Number specified is the slower of the positive and negative slew rates. 7. Input referred, $R_L = 100 \text{ k}\Omega$ connected to V_S/2. Each amp excited in turn with 1 kHz to produce V_O = 3 V_{PP}. (For Supply Voltages < 3 V, $V_{O} = V_{CC}$).

5 V DC ELECTRICAL CHARACTERISTICS (Note 8) Unless otherwise noted, all min/max limits are guaranteed for T _A = 25°C,
V_S = 5 V, V_{CM} = $V_S/2$, V_O = $V_S/2$ and R_L > 1 M Ω . Typical specifications represent the most likely parametric norm.

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Input Offset Voltage	V _{IO}	LMV931 (Single) (-40°C to +125°C)		1	6	mV
	-	LMV932 (Dual) (-40°C to +125°C)		1	7.5	
Input Offset Voltage Average Drift	TCV _{IO}			5.5		μV/°C
Input Bias Current	Ι _Β	-40°C to +125°C		< 1		nA
Input Offset Current	I _{IO}	−40°C to +125°C		< 1		nA
Supply Current (per	I _{CC}	In Active Mode		95	210	μA
Channel)		-40°C to +125°C			230	
Common-Mode	CMRR	0 V \leq V_{CM} \leq 3.8 V, 4.6 V \leq V_{CM} \leq 5.0 V	50	70		dB
Rejection Ratio	-	−40°C to +125°C	50			
	-	-0.2 V \leq V_{CM} \leq 0 V, 5.0 V \leq V_{CM} \leq 5. 2V	50	70		
Power Supply	PSRR	1.8 V \leq V^+ \leq 5 V, V_{CM} = 0.5 V	50	70		dB
Rejection Ratio	-	−40°C to +125°C	50			
Input Common-Mode Voltage Range	Vсм	For CMRR ≥50 dB and T_A = 25°C	V _{EE} - 0.2	-0.2 to 5.3	V _{CC} + 0.2	V
		For CMRR ≥50 dB and T_A = $-40^\circ C$ to $+85^\circ C$	V _{EE}		V _{CC}	1
		For CMRR \geq 50 dB and T _A = -40°C to +125°C	V _{EE} + 0.3		V _{CC} - 0.3	
Large Signal Voltage Gain LMV931 (Single)	Av	R_L = 600 Ω to 2.5 V, V_O = 0.2 V to 4.8 V	88	102		dB
		−40°C to +125°C	87			
		R_L = 2 k Ω to 2.5 V, V_O = 0.2 V to 4.8 V	94	113		
	-	−40°C to +125°C	93			
Large Signal Voltage	A _V	R_L = 600 Ω to 2.5 V, V_O = 0.2 V to 4.8 V	81	90		
Gain LMV932 (Dual)	-	−40°C to +125°C	78			
		R_L = 2 k Ω to 2.5 V, V_O = 0.2 V to 4.8 V	85	100		
	-	−40°C to +125°C	82			
Output Swing	V _{OH}	R_L = 600 Ω to 2.5 V, V_{IN} = \pm 100 mV	4.855	4.89		V
		-40°C to +125°C	4.835			
	V _{OL}	R_L = 600 Ω to 2.5 V, V_{IN} = \pm 100 mV		0.12	0.16	
	-	−40°C to +125°C			0.18	
	V _{OH}	R_L = 2 k Ω to 2.5 V, V_{IN} = $\pm100~mV$	4.945	4.967		
	-	−40°C to +125°C	4.935			
	V _{OL}	R_L = 2 k Ω to 2.5 V, V_{IN} = $\pm100~mV$		0.037	0.065	
		-40°C to +125°C	1		0.075	
Output Short-Circuit	Ι _Ο	Sourcing, Vo = 0 V, V_{IN} = +100 mV	55	65		mA
Current		-40°C to +125°C	45			
		Sinking, Vo = 5 V, V_{IN} = -100 mV	58	80		
		-40°C to +125°C	45			

8. Guaranteed by design and/or characterization.

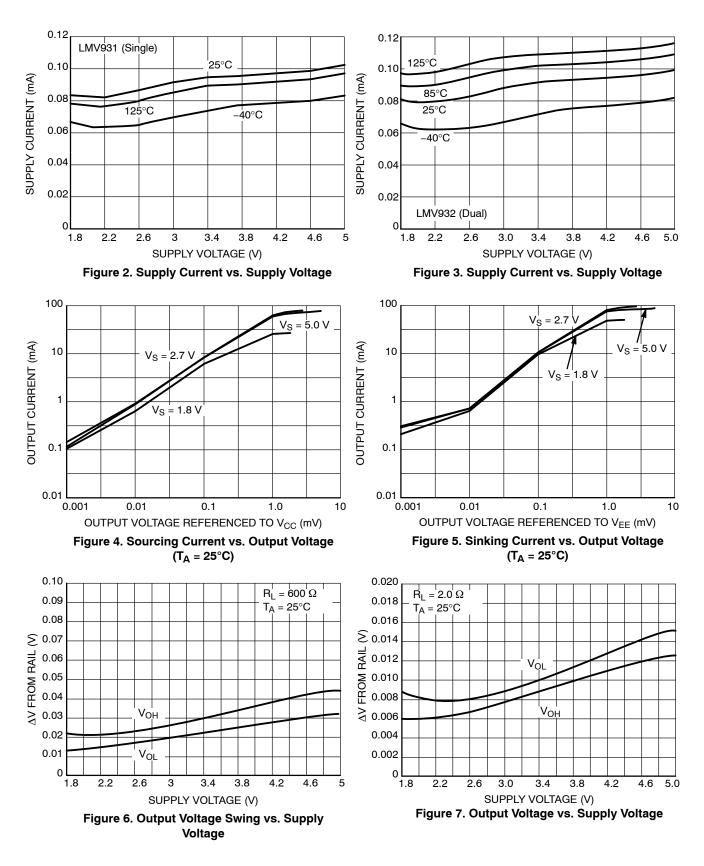
5 V AC ELECTRICAL CHARACTERISTICS Unless otherwise specified, all limits are guaranteed for $T_A = 25^{\circ}C$, $V_S = 5 V$,
$V_{CM} = V_S/2$, Vo = $V_S/2$ and $R_L > 1 M\Omega$. Typical specifications represent the most likely parametric norm.

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Slew Rate	SR	(Note 9)		0.48		V/uS
Gain Bandwidth Product	GBWP			1.5		MHz
Phase Margin	Θm			65		0
Gain Margin	Gm			8		dB
Input-Referred Voltage Noise	e _n	f = 50 kHz, V_{CM} = 2 V		50		nV/√Hz
Total Harmonic Distortion	THD	f = 1 kHz, A _V = +1, R _L = 600 Ω , V _O = 1 V _{PP}		0.022		%
Amplifier-to- Amplifier Isolation		(Note 10)		123		dB

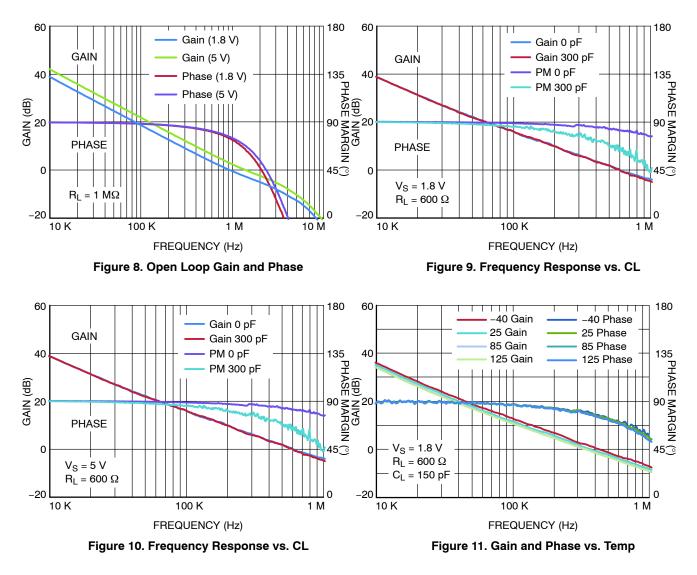
9. Connected as voltage follower with input step from V_{EE} to V_{CC} . Number specified is the slower of the positive and negative slew rates. 10. Input referred, $R_L = 100 \text{ k}\Omega$ connected to $V_S/2$. Each amp excited in turn with 1 kHz to produce $V_O = 3 \text{ V}_{PP}$. (For Supply Voltages < 3 V, $V_O = V_{CC}$).

TYPICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ and } V_S = 5 \text{ V unless otherwise specified})$



TYPICAL CHARACTERISTICS



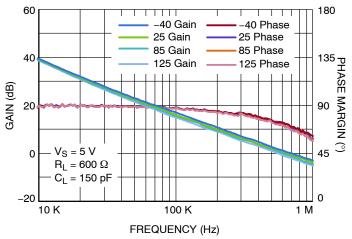
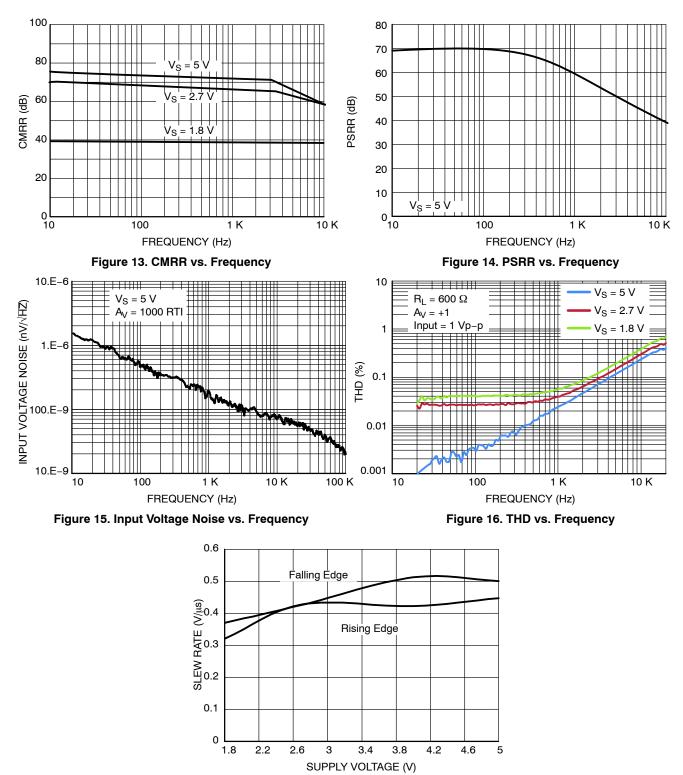


Figure 12. Gain and Phase vs. Temp

TYPICAL CHARACTERISTICS





TYPICAL CHARACTERISTICS

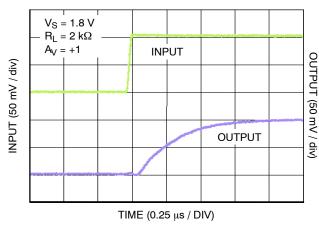


Figure 18. Small Signal Transient Response

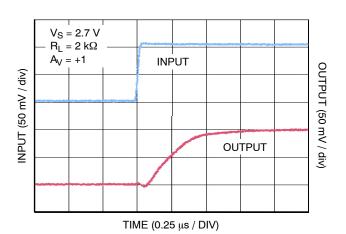


Figure 19. Small Signal Transient Response

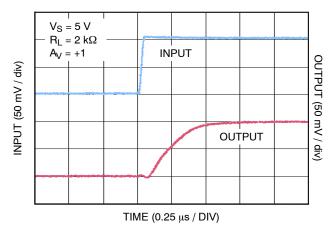
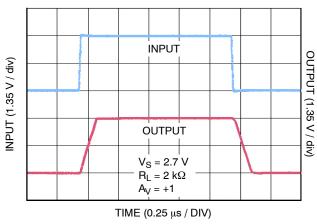


Figure 20. Small Signal Transient Response





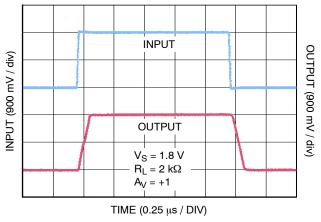
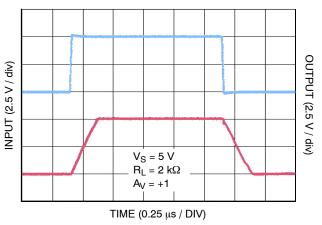
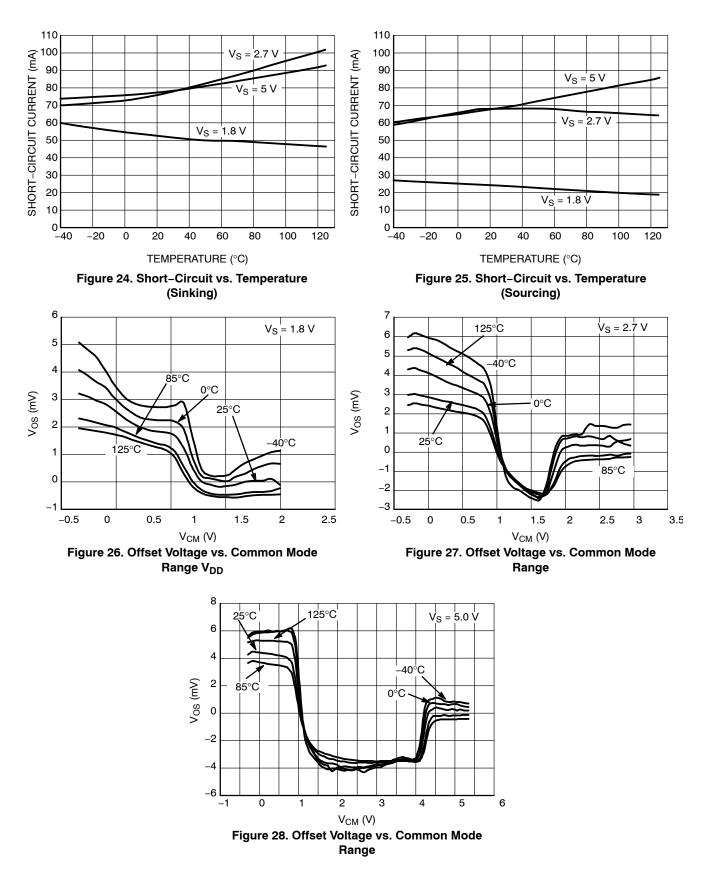


Figure 21. Large Signal Transient Response

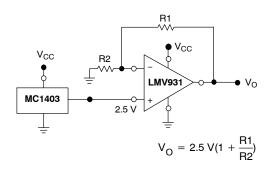




TYPICAL CHARACTERISTICS



APPLICATION INFORMATION





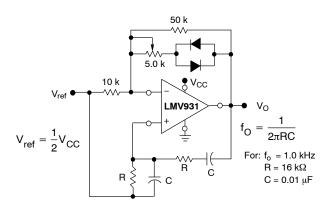
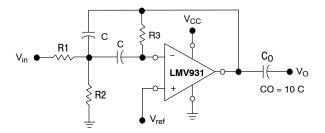


Figure 30. Wien Bridge Oscillator



R2 Hysteresis VOH R1 Vo V_{ref} $\Lambda \Lambda /$ LMV931 V_{O} V_{in} Voi V_{inL} V_{inH} V_{ref} $V_{in}L = \frac{R1}{R1 + R2} \quad (V_{OL} - V_{ref}) + V_{ref}$
$$\begin{split} V_{in}H &= \frac{R1}{R1+R2} \quad (V_{OH}-V_{ref)}+V_{ref} \\ H &= \frac{R1}{R1+R2} \quad (V_{OH}-V_{OL}) \end{split}$$

Figure 31. Comparator with Hysteresis

Given: f_o = center frequency $A(f_o)$ = gain at center frequency

Choose value f_o, C
Then : R3 =
$$\frac{Q}{\pi f_O C}$$

R1 = $\frac{R3}{2 A(f_O)}$
R2 = $\frac{R1 R3}{4 Q^2 B1 - B3}$

For less than 10% error from operational amplifier, (($Q_0 f_0$)/BW) < 0.1 where f_o and BW are expressed in Hz. If source impedance varies, filter may be preceded with voltage follower buffer to stabilize filter parameters.

Figure 32. Multiple Feedback Bandpass Filter

Order Number	Number of Channels	Number of Pins	Package Type	Shipping [†]
LMV931SQ3T2G	Single	5	SC70–5 (Pb–Free)	3000 / Tape & Reel
LMV931SN3T1G	Single	5	TSOP-5 (Pb-Free)	3000 / Tape & Reel
LMV932DMR2G	Dual	8	Micro8 (Pb–Free)	4000 / Tape & Reel
LMV932DR2G	Dual	8	SOIC-8 (Pb-Free)	2500 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ORDERING INFORMATION

0

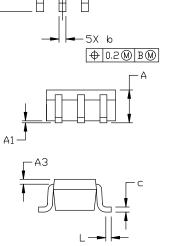
DATE 11 APR 2023



SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE M

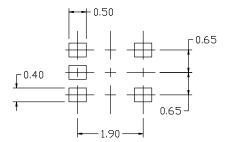
NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. 419A-01 DBSDLETE. NEW STANDARD 419A-02
- 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.



e

F1



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

DIM	MILLIMETERS			
	MIN.	NDM,	MAX.	
А	0.80	0.95	1.10	
A1			0.10	
AЗ	0.20 REF			
b	0.10	0.20	0.30	
С	0.10		0.25	
D	1.80	2.00	2.20	
E	2.00	2.10	2,20	
E1	1.15	1.25	1.35	
e	0.65 BSC			
L	0.10	0.15	0.30	

GENERIC MARKING





*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

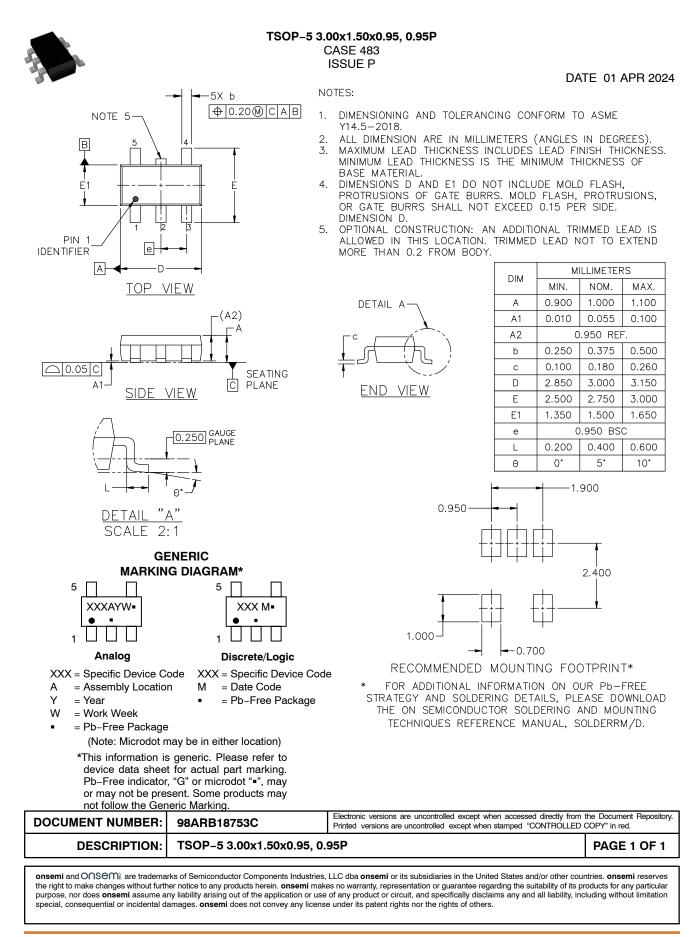
XXX = Specific Device Code

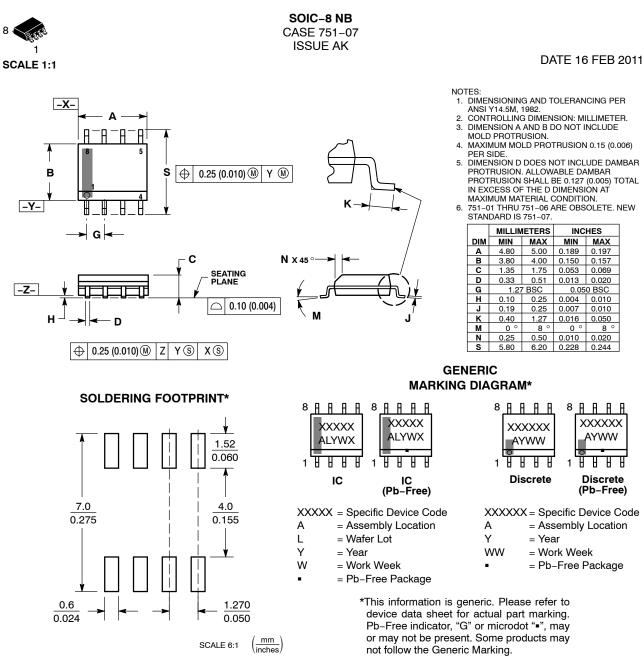
M = Date Code = Pb-Free Package

(Note: Microdot may be in either location)

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STYLE 6: PIN 1. EMITTER 2 2. BASE 2 3. EMITTER 1 4. COLLECTOR 5. COLLECTOR 2/BASE	STYLE 7: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 1 5. COLLECTOR	STYLE 8: PIN 1. CATHODE 2. COLLECTOR 3. N/C 4. BASE 5. EMITTER	STYLE 9: PIN 1. ANODE 2. CATHODE 3. ANODE 4. ANODE 5. ANODE	Note: Please refer to style callout. If style to out in the datasheet r datasheet pinout or p	ype is not called refer to the device
STYLE 1: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR	STYLE 2: PIN 1. ANODE 2. EMITTER 3. BASE 4. COLLECTOR 5. CATHODE	STYLE 3: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. CATHODE 1	STYLE 4: PIN 1. SOURCE 1 2. DRAIN 1/2 3. SOURCE 1 4. GATE 1 5. GATE 2	STYLE 5: PIN 1. CATHODE 2. COMMON ANOD 3. CATHODE 2 4. CATHODE 3 5. CATHODE 4	E

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*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR 3. 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN З. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT 6. IOUT IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. 8. CATHODE STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT 2 OVI 0 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE

6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK

7. VOULK 8. VIN

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SOURCE 1/DRAIN 2

7.

8. GATE 1

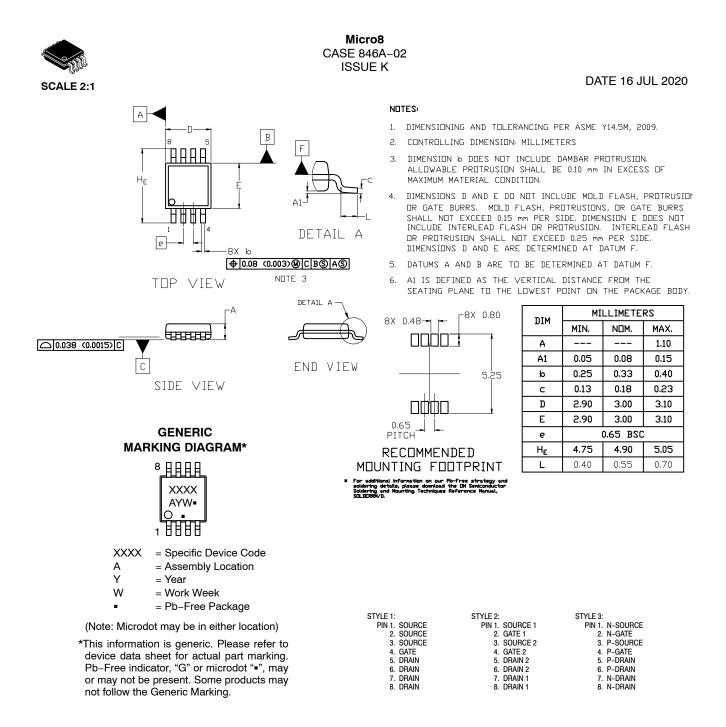
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7.

8

COLLECTOR, #1

COLLECTOR, #1



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